To all our customers

Regarding the change of names mentioned in the document, such as Mitsubishi Electric and Mitsubishi XX, to Renesas Technology Corp.

The semiconductor operations of Hitachi and Mitsubishi Electric were transferred to Renesas Technology Corporation on April 1st 2003. These operations include microcomputer, logic, analog and discrete devices, and memory chips other than DRAMs (flash memory, SRAMs etc.) Accordingly, although Mitsubishi Electric, Mitsubishi Electric Corporation, Mitsubishi Semiconductors, and other Mitsubishi brand names are mentioned in the document, these names have in fact all been changed to Renesas Technology Corp. Thank you for your understanding. Except for our corporate trademark, logo and corporate statement, no changes whatsoever have been made to the contents of the document, and these changes do not constitute any alteration to the contents of the document itself.

Note : Mitsubishi Electric will continue the business operations of high frequency & optical devices and power devices.

Renesas Technology Corp. Customer Support Dept. April 1, 2003



DESCRIPTION

The M61324SP is a semiconductor integrated circuit for the RGBHV interface. The device features swiching signals input from two types of image sources and outputting the signals to the CRT display,etc. Synchronous signals, meeting a frequency band of 10KHz to 200KHz, are output at TTL. The frequency band of video signals is 250MHz, acquiring high-resolution images, and are optimum as an interface IC with high-resolution CRT display and various new media.

The M61324SP keeps the power saving mode, and it can reduce ICC about 10mA under the condition that all Vcc are supplied.

FEATURES

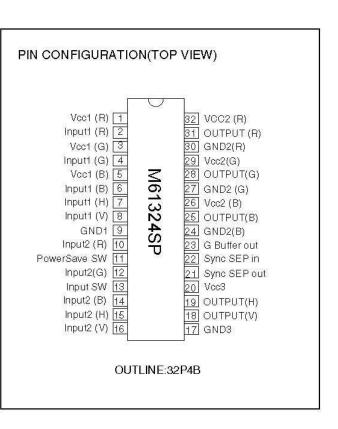
Frequency band : RGB	250MHz
: H,V	
Input level:RGB	0.7Vp-p(Typ.)
H,V TTL input	3 to 5Vo-p (bipolar)
Only the G channel is provided w	with Sync-on video output.
THe TTL format is adopted for H	IV output.

APPLICATION

Display monitor

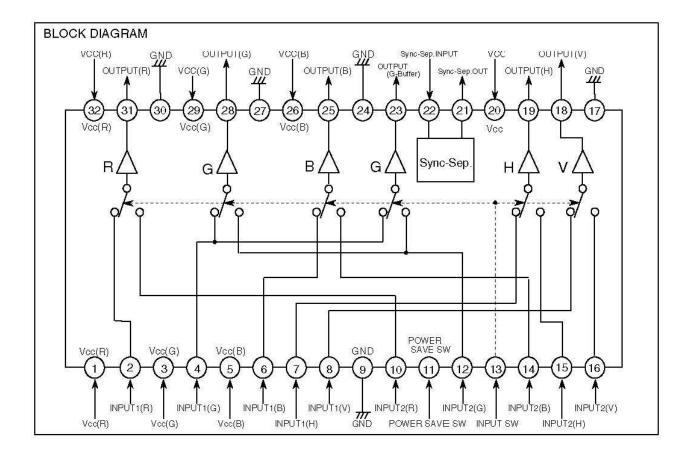
RECOMMENDED OPERATING CONDITION

Supply voltage range	4.75 to 5.25V
Rated voltage range	5.0V











ABSOLUTE MAXMUM RATINGS (Ambient temperature: 25 °C)

Parameter	Symbol	Rating	Unit
Supply voltage	Vcc	7.0	V
Power dissipation	Pd	1603	m₩
Operating temperature	Topr	-20 to +80	°C
Storage temperature	Tstg	-40 to +150	°C
Electroststic discharge	Surge	+200	V
Recommended supply voltage	Vopr	5.0	V
Recommended sopply voltage range	Vopr'	4.75 to 5.25	V

ELECTRICAL CHARACTERISTICS (VCC=5.0V Ta = 25°C)

							Te	est co	nditio	ns							10.7107-04-53N		iŝ
		Test						Input	t					S	W	-	Limits	š	
Symbol	Parameter	point (S)	SW2 Rin1	SW4 Gin1	SW6 Bin1	SW7 Hin1	SW8 Vin1	SW10 Rin2	SW12 Gin2	SW14 Bin2	SW15 Hin2	SW16 Vin2	SW22 Sync	SW11 P.sav	SW13 Switch	Min.	Тур.	Max.	Unit
lcc	Circuit current 1	-	b	b	b	b	b	b	Ь	b	b	b	b	a 3V	b		50	-	mA
IccSTBY	Circuit current 2	-	þ	b	b	b	þ	b	þ	b	b	þ	þ	b	b	Ţ		10	mA
(RG	BSW)																		
Vdc1	Output DC voltage 1	31 28 25	þ	b	b	b	b	b	b	b	b	b	b	a 3V	þ	_	1.5		V
Vdc2	Output DC voltage 2	31 28 25	b	b	b	b	b	b	b	b	b	b	b	a 3V	a 3V	-	1.5	00	v
Vdc3	Output DC voltage 3	23	b	b	b	b	b	b	b	b	b	b	b	a 3V	b		0.9	2 22	v
Vdc4	Output DC voltage 4	23	b	b	b	b	b	b	b	b	b	b	b	a 3V	a 3V	-	0.9	s—:	V
VIMAX1	Maximum allowable input level 1	31 28 25	abb SG1	bab SG1	bba SG1	b	b	b	b	b	b	b	b	a 3V	b	0 10 1-01 8	1.8	3 4:	Vp-p
VIMAX2	Maximum allowable input level 2	31 28 25	b	b	b	b	b	abb SG1	bab SG1	bba SG1	b	b	b	a 3V	a 3V	-	1.8		Vp-p
GV1	Voltage gain 1	31 28 25	abb SG2	bab SG2	bba SG2	b	b	b	b	b	b	b	b	a 3V	b	-0.1	0.7	1.3	dB
∆GV1	Relative voltage gain 1			Rela	tive to	omea	asure	d val	uesa	bove						-0.4	0	0.4	dB
GV2	Voltage gain 2	31 28 25	b	b	b	b	b	abb SG2	bab SG2	bba SG2	b	b	b	a 3V	a 3V	-0.1	0.7	1.3	dB
∆GV2	Relative voltage gain 2	<u> 11 - 11</u>		Relative to measured values above									-0.4	0	0.4	dB			
GV3	Voltage gain 3	23	þ	a SG2	b	b	b	b	b	b	b	b	b	a 3V	þ	-0.6	Ö	0.6	dB
GV4	Voltage gain 4	23	b	b	b	b	b	b	a SG2	b	b	b	b	a 3V	a 3V	-0.6	0	0.6	dB

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ELECTRICAL CHARACTERISTICS (cont.)

		a n asara					্	est co		ons				1 840	2034	ž.	Limits	i i	
Sumbol	Daramotor	Test point	<u>je</u>	and the second	NOS DARIAS			Input I			-	9	C	10 - 10 - 10 - 10 - 10 - 10 - 10 - 10 -	W		1200000000	ar .	
Symbol	Parameter	(S)	SW2 Rin1	SW4 Gin1	SW6 Bin1	SW7 Hin1	SW8 Vin1	SW10 Rin2	SW12 Gin2	SW14 Bin2	SW15 Hin2	SW16 Vin2	SW22 Sync	SW11 P.sav	SW13 Switch	Min.	Тур.	Max.	Unit
Fc1	Freq.characteristic1 (100MHz)	31 28 25	abb SG4	bab SG4	bba SG4	b	b	b	b	b	Б	b	b	a 3V	b	-1	0	3	dB
∆Fc1	Relative Freq.characteristic1 (100MHz)	-		Rela	tive t	o me	asure	d va	lues a	above						~Ĩ	0		dB
Fc2	Freq.characteristic2 (100MHz)	31 28 25	b	b	b	b	b	abb SG4	bab SG4	bba SG4	b	b	b	a 3V	a 3V	-1	0	1	dB
∆Fc2	Relative Freq.characteristic2 (100MHz)	×—		Rela	tive ti	o mea	asure	d val	uesa	bove						Ŧ	0	đ	dB
Fc3	Freq.characteristic3 (200MHz)	31 28 25	abb SG5	bab SG5	bba SG5	þ	b	b	b	b	b	b	b	a 3V	b	-3	27-14	3 	dB
Fc4	Freq.characteristic4 (200MHz)	31 28 25	b	þ	b	b	þ	abb SG5	bab SG5	bba SG5	þ	þ	þ	a 3V	a 3V	-3	s <u>—</u> s	2	dB
CTI1	Crosstalk between two inputs1 (10MHz)	31 28 25	abb SG3		bba SG3	b	b	b	b	b	b	b	b	a 3V	a 3V	-	-60	-45	dB
CTI2	Crosstalk between two inputs2 (10MHz)	31 28 25	b	b	b	b	b	abb SG3	bab SG3	bba SG3	b	b	b	a 3V	b		-60	-45	dB
CTI3	Crosstalk between two inputs3 (100MHz)	31 28 25	abb SG4	bab SG4	bba SG4	þ	b	b	þ	þ	b	þ	b	a 3V	a 3V	1	-40	-30	dB
CTI4	Crosstalk between two inputs4 (100MHz)	31 28 25	b	b	b	b	b	abb SG4	bab SG4	bba SG4	b	b	b	a 3V	b		-40	-30	dB
CTC1	Crosstalk between channels1 (10MHz)	31 28 25	abb SG3	bab SG3	bba SG3	b	b	b	þ	þ	þ	þ	b	a 3V	b		-50	-40	dE
CTC2	Crosstalk between channels2 (10MHz)	31 28 25	b	b	b	b	b	abb SG3	bab SG3	bba SG3	b	b	b	a 3V	a 3V	-	-50	-40	dB
СТСЗ	Crosstalk between channels3 (100MHz)	31 28 25	abb SG4		bba SG4	b	b	b	b	b	b	b	b	a 3V	b	<u>101-1</u> 4	-30	-25	dB
CTC4	Crosstalk between channels4 (100MHz)	31 28 25	b	b	þ	b	b	abb SG4	bab SG4	bba SG4	b	þ	b	a 3V	a 3V	-	-30	-25	dE
Tr1	Distant	31 28 25	abb SG6	bab SG6	bba SG6	b	þ	b	b	b	b	þ	þ	a 3V	b	T	1.6	2.5	nse
Tf1	Pulse characteristic1	31 28 25	abb SG6	bab SG6	bba SG6	b	b	b	þ	b	b	b	b	a 3V	b		1.6	2.5	nse
Tr2	Dulas abarratariation	31 28 25	b	b	b	b	b	abb SG6	bab SG6	bba SG6	b	þ	b	a 3V	a 3V		1.6	2.5	nse
Tf2	Pulse characteristic2	31 28 25	b	b	b	þ	b	abb SG6	bab SG6	bba SG6	b	b	b	a 3V	a 3V	<u></u>	1.6	2.5	nse

RENESAS

			0				Te	est co	nditio	ns					3	5	Limits	0	1
		Test point	6 2					Inpu	ut					SI			Limits		
Symbol	Parameter	(S)	SW2 Rin1	SW4 Gin1	SW6 Bin1	SW7 Hin1	SW8 Vin1	SW10 Rin2	SW12 Gin2	SW14 Bin2	SW15 Hin2	SW16 Vin2	SW22 Sync	SW11 P.sav	SW13 Switch	Min.	Тур.	Max.	Unit
(H)	(HV SW)																		
Vdch1	High level output voltage 1	18 19	b	b	b	a SG8	a SG8	b	b	b	b	b	b	a 3V	b	3.8	4.2	-	V
Vdch2	High level output voltage 2	18 19	b	b	b	b	b	þ	b	þ	a SG8	a SG8	b	a 3V	a 3V	3.8	4.2	4 <u>7-</u> 178	V
Vdcl1	Low level output voltage 1	18 19	b	b	b	a SG8	a SG8	b	b	b	b	b	b	a 3V	b	_	0.2	0.5	v
Vdcl2	Low level output voltage 2	18 19	b	b	b	b	b	b	b	b	a SG8	a SG8	b	a 3V	a 3V		0.2	0.5	V
VithH	Input threshold voltage H	18 19	b	b	b	a SG8	a SG8	b	b	b	b	b	b	a 3V	b	1.8	2.0	2.2	V
VithL	Input threshold voltage L	18 19	b	b	b	a SG8	a SG8	b	b	b	b	b	b	a 3V	b	1.0	1.4	1.6	V
Tr3	Rising time 3	18 19	b	b	b	a SG8	a SG8	b	b	b	b	b	b	a 3V	b	-	25	-	nsec
Tf3	Falling time 3	18 19	b	b	b	a SG8	a SG8	b	b	b	b	b	b	a 3V	b	1	15	3 <u></u>	nsec
HVdr	Rising deley time	18 19	b	b	b	a SG8	a SG8	b	b	b	b	b	b	a 3V	b		40	60	nsec
HVDf	Falling deley time	18 19	b	b	b	a SG8	a SG8	b	b	b	b	b	b	a 3V	b	<u>10</u> 0	40	60	nsec
(S)	(NC SEP.)																		
SYrv	Sync on G input minimum voltage	21	b	b	b	b	b	b	b	b	b	b	a SG7	a 3V		0.2	s :— s	6 81	Vp-p
SYVH	Sync output high level voltage	21	b	b	b	b	b	b	b	b	b	b	a SG7	a 3V		3.8	4.3	-	v
SYVL	Sync output low level voltage	21	b	b	b	b	b	b	b	b	b	b	a SG7	a 3V	-	Ι	0.2	0.5	V
STr	Sync output rising time 3	21	b	b	b	b	b	b	b	b	b	b	a SG7	a 3V	_	-	25	<u></u>	nsec
STf	Sync output falling time 3	21	b	b	b	b	b	b	þ	b	b	b	a SG7	a 3V	<u> </u>	I	15		nsec
SDr	Sync output rising deley time	21	b	b	b	b	b	þ	b	b	b	b	a SG7	a 3V	<u> </u>	_	40	60	nsec
SDf	Sync output falling deley time	21	b	b	b	b	b	b	b	b	b	b	a SG7	a 3V	<u></u>	-	40	60	nsec
(Cł	HANNEL SERECT S	N , PC	DWE	R SA	VE S	SW)												÷	
Vthch1	Channel select SW threshold voltage 1		a SG6	a SG6	a SG6	a SG8	a SG8	b	b	b	b	b	a SG7	a 3V	a variable	2.5	3. 	la-to	٧
Vthch2	Channel select SW threshold voltage 2	<u> - 1</u> 2	a SG6	a SG6	a SG6	a SG8	a SG8	b	b	b	b	b	a SG7	a 3V	a variable	I.	-	1.0	٧
VthPH	Power save SW threshold voltage 1	H	a SG6	a SG6	a SG6	a SG8	a SG8	b	b	b	þ	b	a SG7	a variable	b	2.0	s.—		ν
VthPL	Power save SW threshold voltage 2	-	a SG6	a SG6	a SG6	a SG8	a SG8	b	b	b	b	b	a SG7	a variable	b	61-70	<u>. </u>	1.0	V

ELECTRICAL CHARACTERISTICS (cont.)



ELECTRICAL CHARACTERISTICS TEST METHOD

Circuit current 1

No signal. Measure the total circuit current as Icc when supplying 3VDC to Pin11.

Circuit current 2

No signal. Measure the total circuit current as IccSTBY when Pin11 connected to GND.

Output DC voltage 1,2

Set SW13 to GND (or OPEN), measure the DC voltage of TP31(TP28,TP25) when there is no signal input. The DC voltage is as vdc1(vdc2).

Output DC voltage 3,4

Measure the DC voltage TP23 same as "Output DC voltage 1,2". The DC voltage is Vdc3(Vdc4).

Maximum allowableinput level 1,2

Set SW13 to GND, input SG1 to Pin2 only. Gradually increasing the SG1 amplitude, read the amplitude of the input signal when the output waveform of TP31 is strained. The value is as Vimer1. In the same way, measure Vimer1 in response to inputs in Pin4 and Pin6 only.

Then set SW13 to OPEN, measure Vimes2 in response to inputs in Pin10,12 and 14 only.

Voltage gain 1,2

1. The conditions is as table.

2. Set SW13 to GND, input SG2(0.7Vp-p) to Pin2 only. Read the output amplitude of TP31. The value is as VoR1.

(dB)

3. Voltage gain Gv1 is

4. In the same way, calculate Gv1in response to inputs in Pin4 and Pin6 only.

5. Then set SW13 to OPEN, measure Gv2 in response to inputs in Pin10,12 and 14 only.

Relative voltage gain 1,2

1. Calculate relative voltage gain ΔG_{V1} by the following formula.

 Δ Gv1=Gv1R-Gv1G, Gv1G-Gv1B, Gv1B-Gv1R

2. In the same way, calculate $\Delta Gv2$.

Voltage gain 3,4

1. The conditions is as table.

2. Read the output amplitude of TP23.

3. Calculate Gv3, Gv14 same as "Voltage gain 1".

Freq.characteristic 1,2 / Relative freq.characteristic 1,2

- 1. The conditions is as table. This measurement shall use active probe.
- 2. Set SW13 to GND, input SG4(0.7Vp-p) to Pin2 only. Measure TP31 output amplitude as Vor1. In the same way,input SG2(0.7Vp-p) to Pin2 only. Measure TP31 output amplitude as Vor2.
- 3. Freq.characteristic1 Fo1 is

$$F_{c1} = 20 \text{ LOG} \frac{V_{OR2} \text{ [Vp-p]}}{V_{OR1} \text{ [Vp-p]}}$$
(dB)

4. In the same way, calculate Fc1 in response to inputs in Pin4 and Pin6 only.

5. The defference between of each channel Freq.characteristic is as $\Delta F_{c}1$.

6. Then set SW13 to OPEN, measure Fc2 and ∆Fc2 in response to inputs in Pin10,12 and 14 only.

Freq.characteristic 3,4

Measure the Fo3, Fo4 when SG5 of input signal. (For reference)



Crosstalk between two inputs 1,2

- 1. The conditions is as table. This measurement shall use active probe.
- 2. Set SW13 to GND, input SG3 to Pin2 only. Read the output amplitude of TP31. The value is as Vor3.
- 3. Then set SW13 to OPEN, read the output amplitude of TP31. The value is as VoR3'.
- 4. Crosstalk between two inputs 1 C.T.I.1 is

$$C.T.I.1 = 20 \text{ LOG} \frac{V_{OR3}' [Vp-p]}{V_{OR3} [Vp-p]} \qquad (dB)$$

- 5. In the same way, calculate C.T.I.1 in response to inputs in Pin4 and Pin6 only.
- 6. Then set SW13 to OPEN, input SG2 to Pin10 only. Read the output amplitude of TP31. The value is as Von4.
- 7. Set SW13 to GND, read the output amplitude of TP31. The value is as Vor4'.
- 8. Crosstalk between two inputs 1 C.T.I.2 is

C.T.I.2= 20 LOG
$$\frac{V_{OR}4'[Vp-p]}{V_{OR}4[Vp-p]}$$
 (dB)

9. In the same way, calculate C.T.I.2 in response to inputs in Pin12 and Pin14 only.

Crosstalk between two inputs 3,4

Set SG4 as the input signal, and then the same method astable, measure C.T.I.3, C.T.I.4. Crosstalk between channels 1,2

- 1. The conditions is as table. This measurement shall use active probe.
- 2. Set SW13 to GND, input SG3 (0.7Vp-p) to Pin2 only. Read the output amplitude of TP31. The value is as Von5.
- 3. Next, measure TP28, TP25 in the same state, and the amplitude is as Vog5, Vog5.
- 4. Crosstalk between channels1 C.T.C1 is

C.T.C1=20 LOG
$$\frac{V_{OG5} \text{ or } V_{OB5}}{V_{OR5}}$$
 (dB)

- 5. In the same way, calculate C.T.C.1 in response to inputs in Pin4 and Pin6 only.
- 6. Then set SW13 to OPEN, input SG3(0.7Vp-p) to Pin10 only.
- Read the output amplitude of TP31. The value is as Vor6.
- 7. Next, measure TP28, TP25 in the same state, and the amplitude is as Vog6, Vog6.
- 8. Crosstalk between two inputs 1 C.T.C.2 is

$$C.T.C2=20 \text{ LOG } \frac{V_{\text{OB}6} \text{ or } V_{\text{OB}6}}{V_{\text{OB}6}} \quad \text{(dB)}$$

9. In the same way, calculate C.T.C.2 in response to inputs in Pin9 and Pin11 only.

Crosstalk between channels 3,4

Set SG4 as the input signal, and then the same method astable, measure C.T.C3, C.T.C4. Pulse characteristic 1,2

- 1. The conditions is as table. (SG5 amplitude 0.7Vp-p) Set SW13 to GND (or OPEN).
- 2. Measure rising Tri and falling Tfi for 10%~90% of the input pulse with active plobe.

3. Next, measure rising Tro and falling Tfo for 10%~90% of the output pulse with active plobe.

4. Pulse characteristic Tr1, Tf1(Tr2, Tf2) is

$$Tr1(Tr2) = \sqrt{(Tro)^2 - (Tri)^2}$$
(nsec)

$$Tf1(Tf2) = \sqrt{(Tfo)^2 - (Tfi)^2}$$
(nsec)

$$0\% \rightarrow T_r \leftarrow T_t \leftarrow$$



	MITSUBISHI ICs <monitor> M61324SP</monitor>
v	WIDE FREQUENCY BAND ANALOG SWITCH
<hv-sw></hv-sw>	
 Hi level output voltage 1,2 / Lo level output voltage 1,2 1. The conditions is as table. Input SG8 to Pin7 (or Pin8). low voltage of TP19, TP18. The value is as Vdch1, Vdcl 2. Input SG8 to Pin15 (or Pin16). Set SW13 to OPEN, rea The value is as Vdch2, Vdcl2. 	Ta
 Input threshold voltage H / Input threshold voltage L 1. Set SW13 to GND (or OPEN). Gradually increasing the voltage of Pin7 (or Pin15) when the TP19 voltage turnd h 2. Gradually decreasing the voltage of Pin7 (or Pin15) from when the TP19 voltage turnd low level (0.5V or less). The 	nigh level (3.8V or more). The value is as VithH. n 3V, measure the input voltage of Pin7 (or Pin15)
3. In the same way, measure the input voltage of Pin8 (or I	
Rising time / Falling time	100%
 The conditions is as table. This measurement shall use a 2. Measure rising Tri and falling Tfi for 20%~80% of the output pulse as Tr3, Tf3 (Tr4, Tf4). 	20'
Rising deley time / Falling deley time	
Set SW13 to GND (or OPEN), input SG8 to Pin7 (or Pin15)
Measure the rising deley time HVdr and the falling deley tin	
In the same way, measure HVdr and HVdf when input SG8 to Pin8 (or Pin16).	HVDr → + HVDf
<sync-separation></sync-separation>	Waveform output
Sync input minimum voltage	
Gradually decreasing the amplitude of SG7 in Pin22, measured	ure the amplitude of SG7 when the Sync-Sep output
signal turn off . The value is as SYrv.	
Sync output High level voltage / Sync output Low level voltage Input SG7 to Pin22, read the output High level and low volt	tage of TP21. The value is as SVV/H_SVV/I
Sync output rising time / Sync output falling time	
1. The conditions is as table. (SG7 amplitude 0.3Vp-p)	100% /90%
This measurement shall use active probe.	
2. Measure rising Tri and falling Tfi for 10%~90%	
of the input pulse as STr, STf .	0%→ ← → ←
Sync output rising deley time	'str istf
Sync output falling deley time	SG7 —
Input SG7 to Pin22. Measure the rising deley time Sdr	-\ 509
and the falling deley time Sdf.	sDr → ← sDf
	Waveform output
<others></others>	New York Contraction of the Cont
Channel select SW threshold 1,2	
 Gradually increasing the voltage of Pin13 from 0V, measing the voltage of Pin13 from 0V, measing the value is as Vthch1. 	27.4 27.4
2.Gradually decreasing the voltage of Pin13 from 5V, measured	sure the minimum voltage of Pin13 when the channel 2

2.Gradually decreasing the voltage of Pin13 from 5V, measure the minimum voltage of Pin13 when the channel 2 is selected. The value is as Vthch2.

Power save SW threshold 1,2

1. Gradually increasing the voltage of Pin11 from 0V, measure the maximum voltage of Pin11 when the Power save mode. The value is as VthPL.

2.Gradually decreasing the voltage of Pin13 from 5V, measure the minimum voltage of Pin11 when the Power save mode. The value is as VthPH.

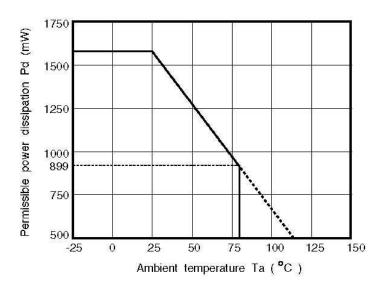
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INPUT SIGNAL

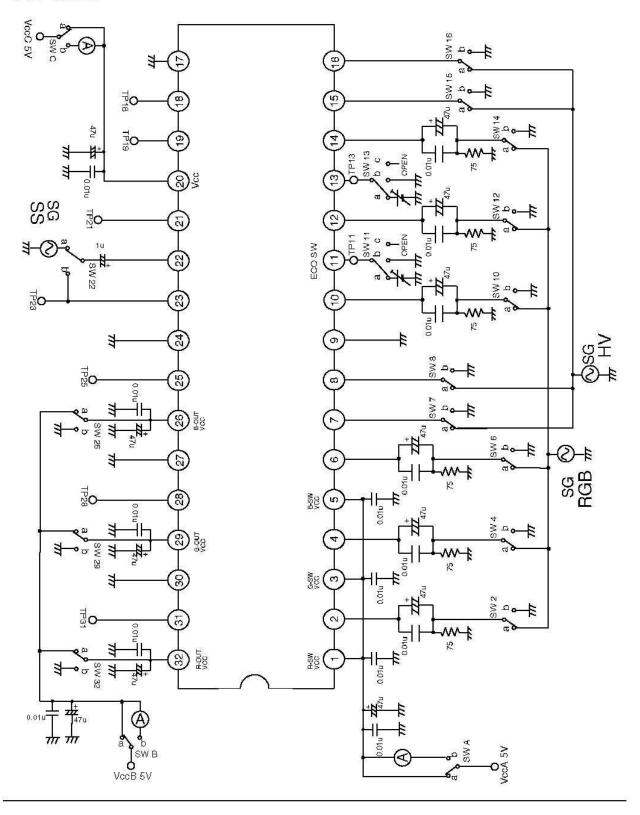
SG1	Sine wave(f=60KHz, 0.7Vp-p(Amplitude variable))
-2	0.7Vp-p (variable)
SG2	Sine wave(f=1MHz, 0.7Vp-p(Amplitude variable))
SG3	Sine wave(f=10MHz, 0.7Vp-p(Amplitude variable))
SG4	Sine wave(f=100MHz, 0.7Vp-p(Amplitude variable))
SG5	Sine wave(f=250MHz, 0.7Vp-p(Amplitude variable))
SG6	
	↓ 0.7Vpp fH=60kHz 0.7Vp-p
SG7	Sync (fH=60KHz)
	Amplitude variable (Typ. =0.3Vp-p) 4.5us
SG8	TTL 5V DUTY=50% fH=60kHz 0V

THERMAL DERATING CURVE



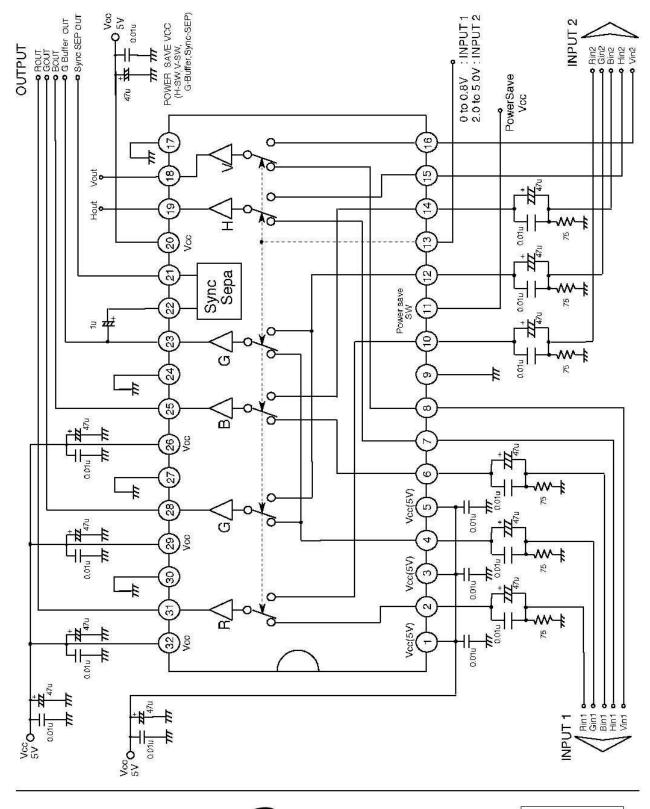
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TEST CIRCUIT



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APPLICATION EXAMPLE



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DISCRIPTION OF PIN

Pin No.	Description	DC Voltage[V]	Peripheral circuits at pins	Notes
1 3 5 20	Vcc(R) Vcc(G) Vcc(B) Vcc(H,V,Sync-Sep.)	5.0	°	
26 29 32	Vcc(ROUT) Vcc(GOUT) Vcc(BOUT)	5.0		
2 4 10 12 14	Input1(R) Input1(G) Input1(B) Input2(R) Input2(G) Input2(B)	2.3		Input signai with Iow impedance.
7 8 15 16	Input1(H) Input1(V) Input2(H) Input2(V)		¢ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓	Input pulse between 3V and 5V.
9 17 24 27 30	GND(V-SW) GND (H,V,Sync-Sep.) GND(B-out) GND(G-out) GND(R-out)	GND		

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DISCRIPTION OF PIN (cont.)

Pin No.	Description	DC Voltage[V]	Peripheral circuits at pins	Notes
11	PwrSave-SW	2.5		Do not apply more 5V DC voltage.
13	CONT-SW	2.4		Do not apply more 5V DC voltage.
18 19	Vout Hout			

RENESAS

Pin No.	Description	DC Voltage[V]	Peripheral circuits at pins	Notes
21	Sync sep OUT			
22	Sync sep IN		10K 10K 10K 2K CLAMPret CLAMPret CLAMPret 0 2K 2K 2K 2L 2L 2L 2L 2L 2L 2L 2L 2L 2L	Connect a capacitance between the pin and GND when not use SYNC-SEP.
23	G Buffer OUT			
25 28 31	Video OUT (B) Video OUT (G) Video OUT (R)	1.5	32,29,26PIN 300 300 31,28,25PIN 30,27,24PIN	

DISCRIPTION OF PIN (cont.)

RENESAS

NOTE HOW TO USE THIS IC

- 1. R,G,B input signal is 0.7Vp-p of standard video signal.
- 2. H,V input is 5.0V TTL type.
- 3. Input signal with sufficient low inpedance to input terminal.
- 4. The terminal of R,G,B output pin are shown as Fig.1. When resistance is connected between the pin31(28,25) and GND, lcc will be increase.
- 5. Swicth(Pin13) can be changed by supplying some voltage as Fig.2.
 0 to 0.5V:INPUT1
 2.5 to 5V:INPUT2
 Do not apply Vcc or more DC voltage.
- 6. Power save mode is provided for saving loc less than about 10mA as Fig.3. 0 to 0.5V:Power save mode (H.V-SW,Sync-Sep.,G-Buffer)
 2.5 to 5V:Normal mode
 Do not apply 5V or more DC voltage.
- 7. When not use the Sync-separation circuit built in this IC, capacitance of several tens of pF is required between the pin22 and GND.

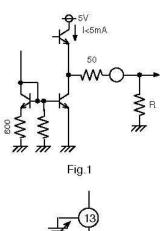








Fig.3

CAUTIONS FOR MANUFACTURING BOARDS

Built-in wide band preamplifier may cause oscillation due to the wiring shape on the board. Be careful for the following points.

Vcc shall use a stable power supply. (Individual Vcc should use an independent power supply.)

GND should be as wide as possible. Basically,solid earth should be used. Make the load capacitance of output pins as small as possible.

Also ground the hold capacitance to stable GND ,wicth is as near to the pin as possible.

Insertion of a resistance of several tens of ohms between the output pin and the circuit at the next stage makes oscillation harder.

When inserting an output pull-down resistance, make wire between the output pin and the resistance as short as possible.



